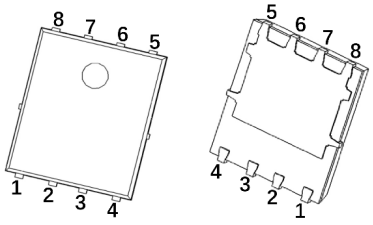
GPT070N10LNC

100V N-Channel MOSFET

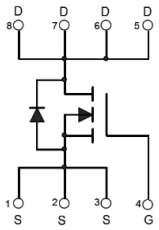
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	8.3mΩ@10V	75A
	11.3mΩ@10V	

PDFN5X6-8L



Schematic diagram



Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application

MARKING:

T070N10L = Device Code

XX = Date Code

Solid Dot = Green Indicater

ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	100	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1,5]	T_C = 25℃	I_D	75	A
	T_C = 100℃		53	
Pulsed Drain Current[2]		I_{DM}	300	A
Single Pulsed Avalanche Current[3]		I_{AS}	31	A
Single Pulsed Avalanche Energy[3]		E_{AS}	144	mJ
Power Dissipation[4,5]	T_C = 25℃	P_D	96	W
Thermal Resistance from Junction to Ambient[6]		$R_{\theta JA}$	55	℃/W
Thermal Resistance from Junction to Case		$R_{\theta JC}$	1.3	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V , I_D = 250μA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	2.0	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D =11.5A		8.3	12	mΩ
		V_{GS} = 4.5V, I_D =9.5A		11.3	16	
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz		2188		pF
Output Capacitance	C_{oss}			514		
Reverse Transfer Capacitance	C_{rss}			23		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		1.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 50V, V_{GS} = 10V, I_D =11.5A		38.5		nC
Gate-source Charge	Q_{gs}			6.5		
Gate-drain Charge	Q_{gd}			9.6		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 50V, V_{GS} = 10V, I_D =20A, R_G =3Ω		15		ns
Turn-on Rise Time	t_r			31		
Turn-off Delay Time	$t_{d(off)}$			58		
Turn-off Fall Time	t_f			15		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = 1A			1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

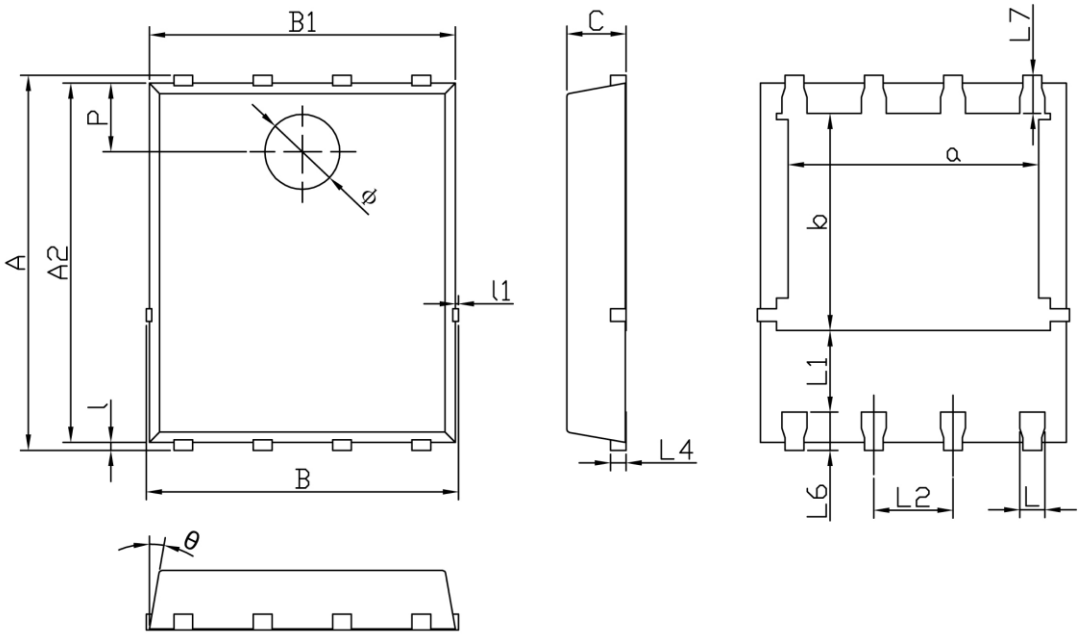
3.E_{AS} condition: V_{DD} = 50V,V_{GS} = 10V, L = 0.3mH, R_G = 25Ω Starting T_J = 25°℃.

4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

PDFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.900	6.100	0.232	0.240
a	3.910	4.110	0.154	0.162
A2	5.700	5.800	0.224	0.228
B	4.900	5.100	0.193	0.201
b	3.370	3.570	0.133	0.141
B1	4.800	5.000	0.189	0.197
C	0.900	1.000	0.035	0.039
L	0.350	0.450	0.014	0.018
l	0.060	0.200	0.002	0.008
L1	1.100	-	0.043	-
l1	-	0.100	-	0.004
L2	1.170	1.370	0.046	0.054
L4	0.210	0.340	0.008	0.013
L6	0.510	0.710	0.020	0.028
L7	0.510	0.710	0.020	0.028
P	1.000	1.200	0.039	0.047
Φ	1.100	1.300	0.043	0.051
θ	8°	12°	8°	12°